



CPH3340 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-20	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm)	1.2	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-2.5A	5.2	8.6		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-2.5A, V _{GS} =-4V		32	45	mΩ
	R _{DS(on)2}	I _D =-1A, V _{GS} =-2.5V		44	62	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		1875		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		289		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-10V, f=1MHz		276		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		21		ns
Rise Time	t _r	See specified Test Circuit.		93		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		178		ns
Fall Time	t _f	See specified Test Circuit.		130		ns

Marking : YP

Continued on next page.

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CPH3340

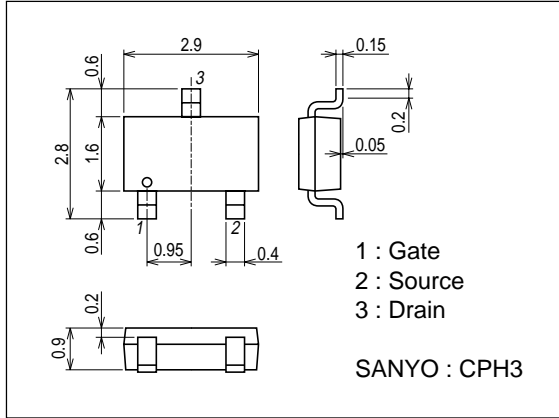
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-4V, I _D =-5A		16		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4V, I _D =-5A		3.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-4V, I _D =-5A		3.2		nC
Diode Forward Voltage	V _{SD}	I _S =-5A, V _{GS} =0V		-0.83	-1.2	V

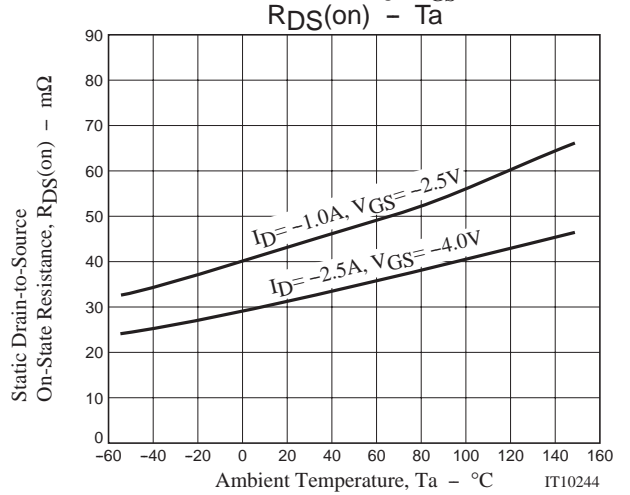
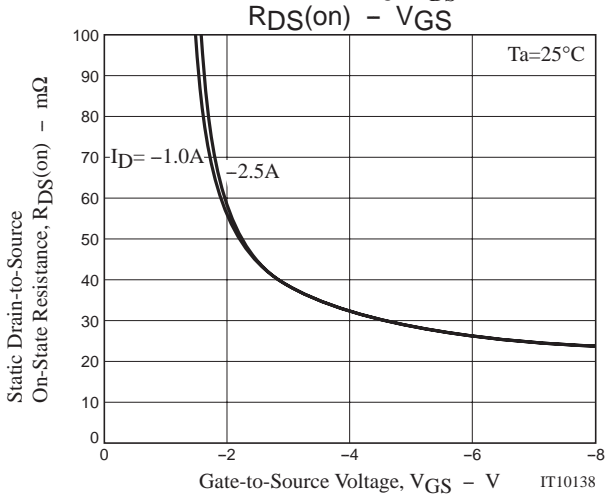
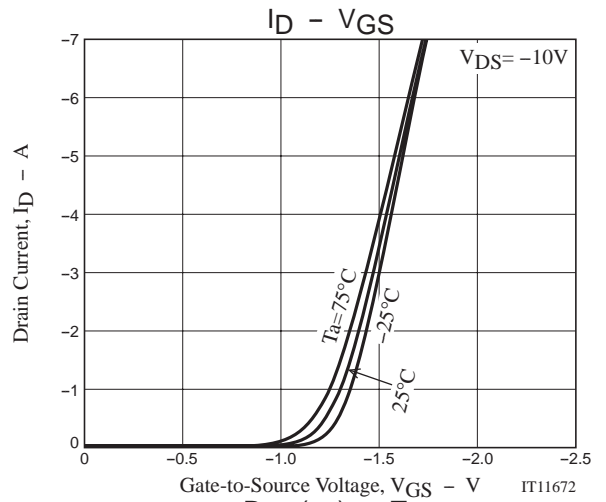
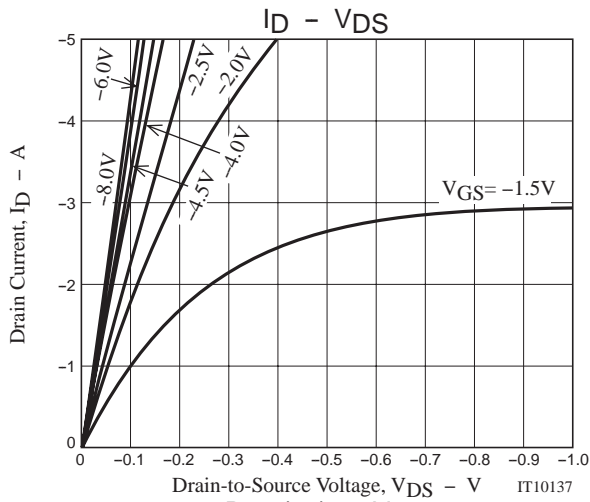
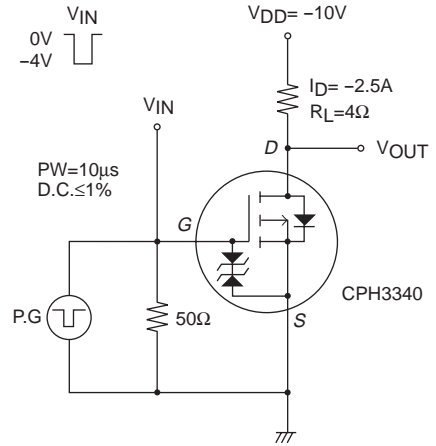
Package Dimensions

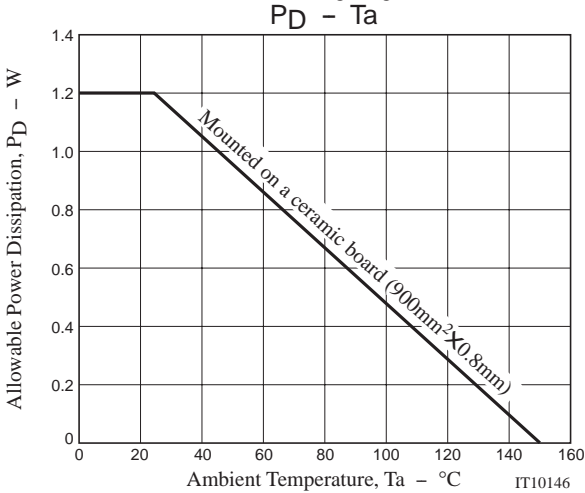
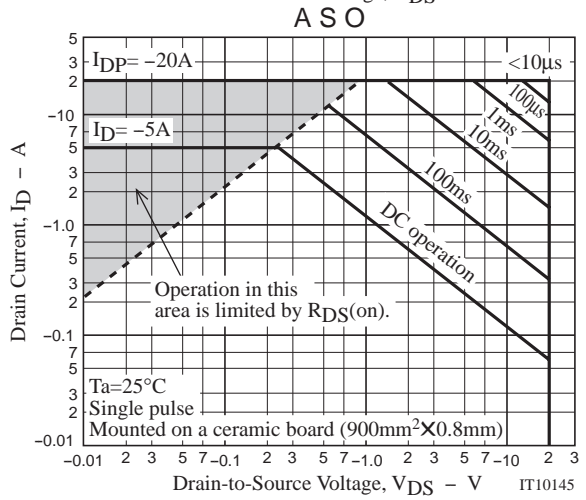
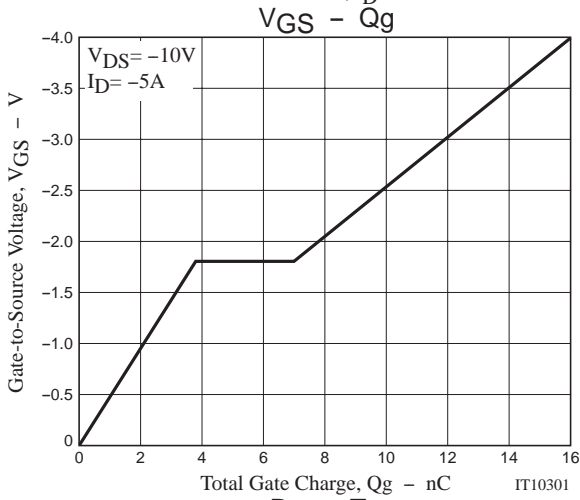
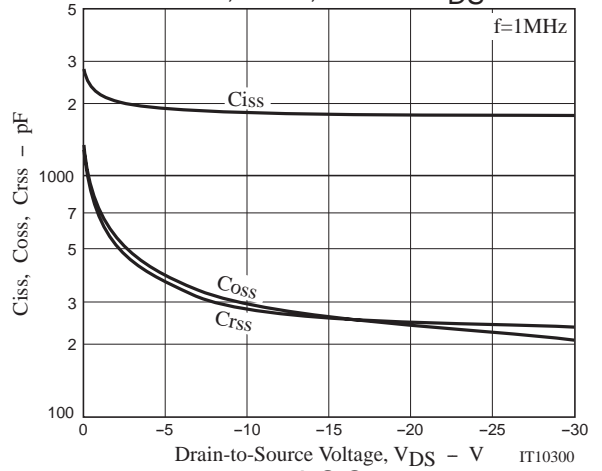
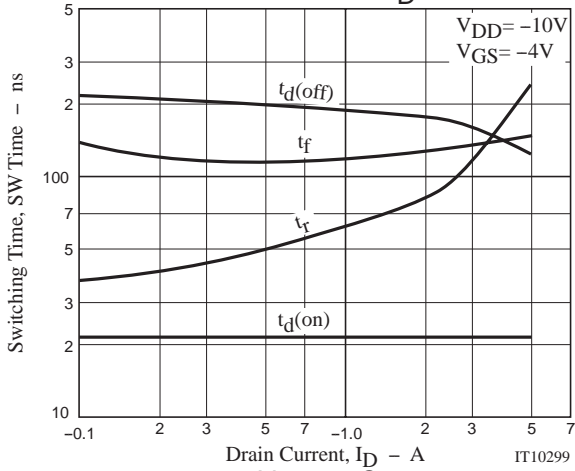
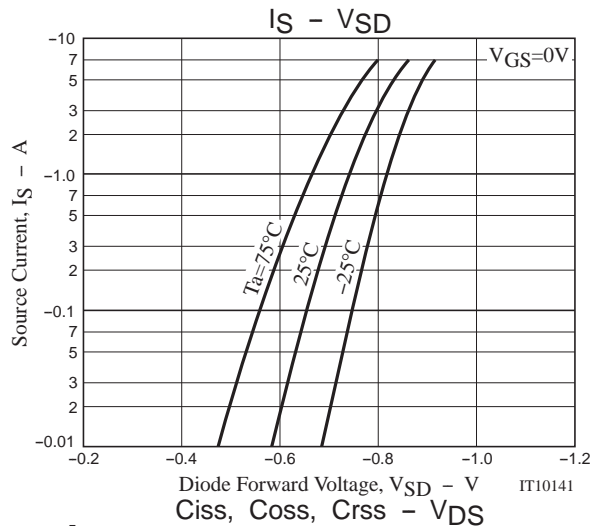
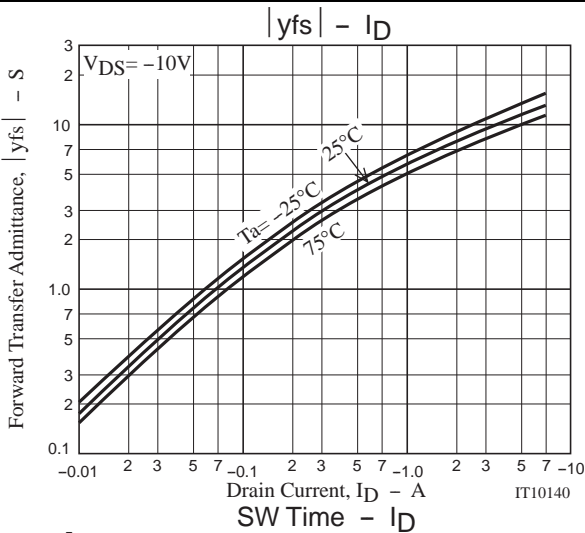
unit : mm (typ)

7015A-004



Switching Time Test Circuit





Note on usage : Since the CPH3340 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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